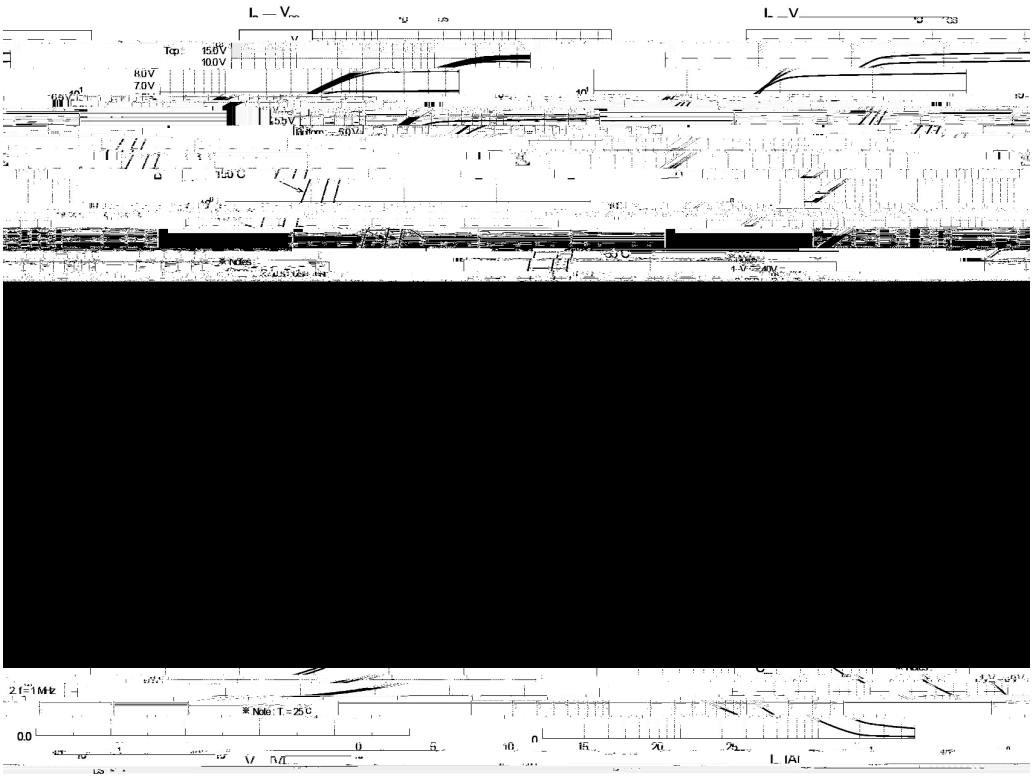
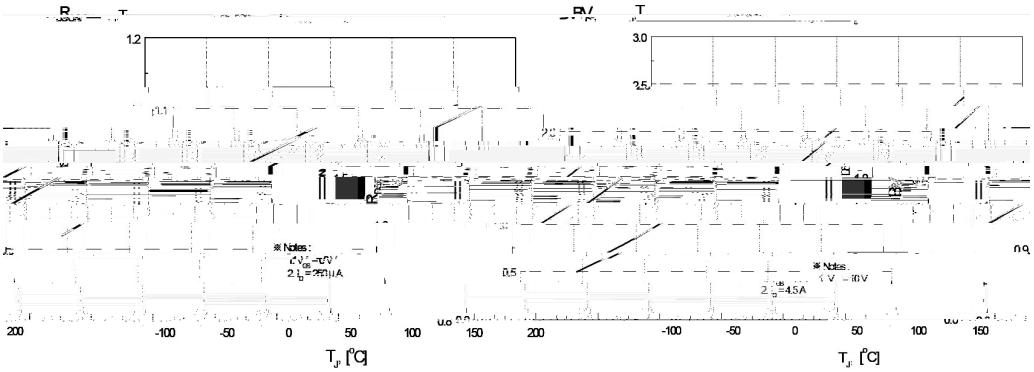
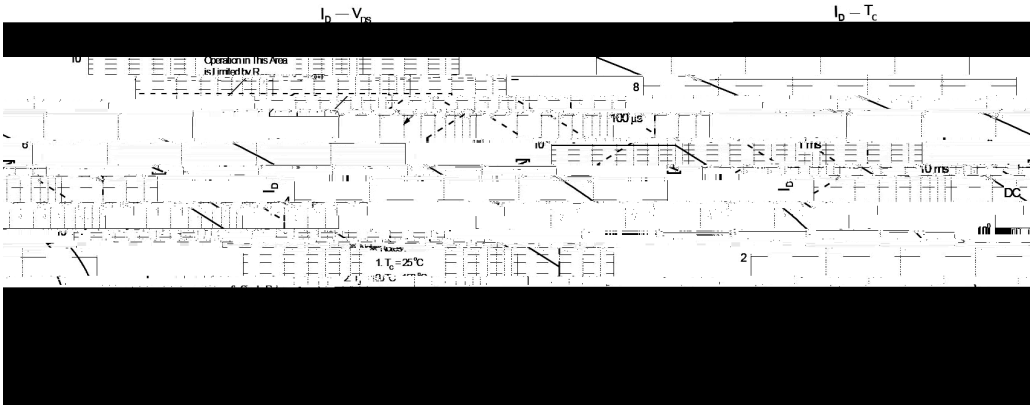
TO-251 ḾḾḃ N

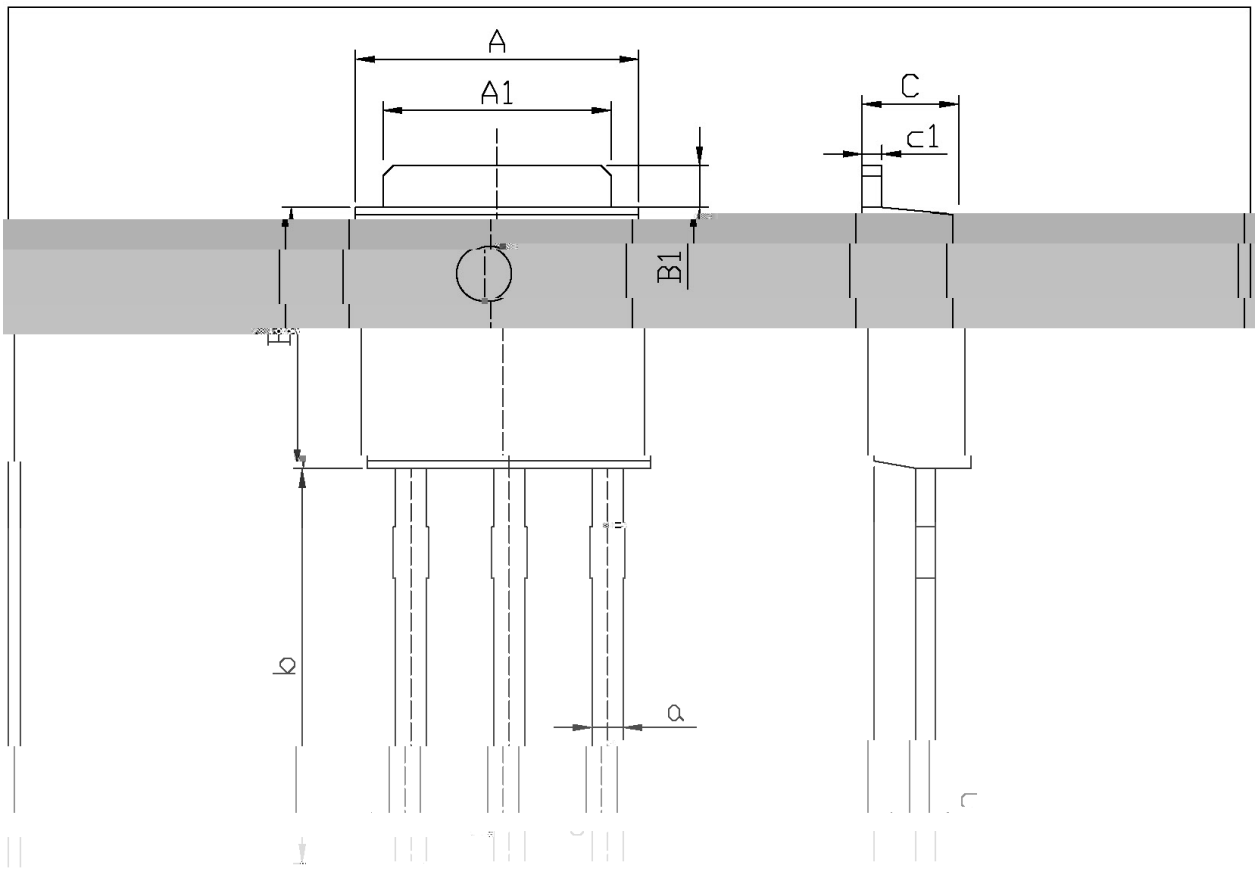
v ̈Ω Parameter	ϒ N Symbol	̈Ω Ö Rating	D Ч Unit
Drain-Source Voltage	V_{DSS}	200	V
Drain Current	$I_{D(Tc=25\ )}$	9	A
Drain Current	$I_{D(Tc=100\ )}$	5.7	A
Drain Current - Pulsed	I_{DM}	36	A
Gate-Source Voltage	V_{GSS}	±30	V
Avalanche Current	I_{AR}	9	A
Single Pulsed Avalanche Energy	E_{AS}	160	mJ
Repetitive Avalanche Energy	E_{AR}	7.2	mJ
Power Dissipation	P_D	3.13	W
Power Dissipation	P_D(Tc=25)	72	W
Operating and Storage Temperature Range	T_J,T_{STG}	-55 to 150	

v ̈Ω Parameter	ϒ N Symbol	⊥ :† ϒ Test Conditions	ω ŋ Ö Min	Ɛ ʒ Ö Typ	ω ² Ö Max	D Ч Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	200			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=200V V_{GS}=0V			10	μA
		V_{DS}=160V T_C=125			100	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±30V V_{DS}=0V			±0.1	μA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS} I_D=250μA	2		4	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=10V I_D=4.5A		0.34	0.4	Ω
Forward Transconductance	g_{FS}	V_{DS}=40V I_D=4.5A		7.05		S
Drain-Source Diode Forward Voltage	V_{SD}	V_{GS}=0V I_S=9A			1.5	V
Input Capacitance	C_{iss}	V_{DS}=25V V_{GS}=0V f=1MHz		550	720	pF
Output Capacitance	C_{oss}			85	110	pF
Reverse Transfer Capacitance	C_{rss}			22	29	pF
Turn-On Delay Time	$t_{d(on)}$	V_{DD}=100V I_D=9A R_G=25Ω		11	30	ns
Turn-On Rise Time	t_r			70	150	ns
Turn-Off Delay Time	$t_{d(off)}$			60	130	ns
Turn-Off Fall Time	t_f			65	140	ns

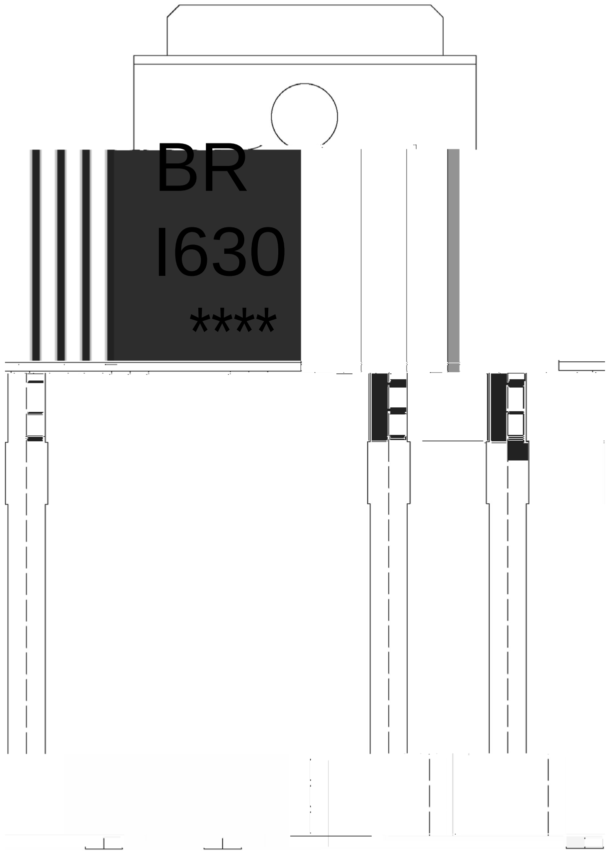








B	5.95	6.25	C	0.45	0.55
B1	0.95	1.25	C1	0.45	0.55



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Note:

BR: Company Code

I630: Product Type.

****: Lot No. Code, code change with Lot No.

Rev.D Nov.-2015